

**SYNCHRONOUS MOSFET CONTROLLER IN SO-8**
**Description**

ZXGD3107N8 synchronous controller is designed for driving a MOSFET as an ideal rectifier. This is to replace a diode for increasing the power transfer efficiency.

Proportional Gate drive control monitors the reverse voltage of the MOSFET such that if body diode conduction occurs, a positive voltage is applied to the MOSFET's Gate pin. Once the positive voltage is applied to the Gate, the MOSFET switches on allowing reverse current flow. The controllers' output voltage is then proportional to the MOSFET drain-source voltage and this is applied to the Gate via the driver. This action minimizes body diode conduction while enabling a rapid MOSFET turn-off as drain current decays to zero.

**Applications**

Flyback Converters in:

- AC-DC Adaptors
- Set-Top Boxes
- PoE Power Devices

Resonant Converters in:

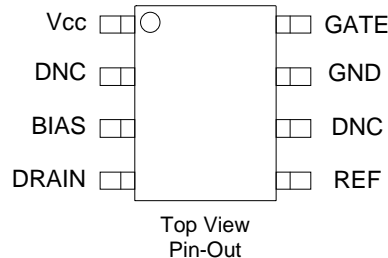
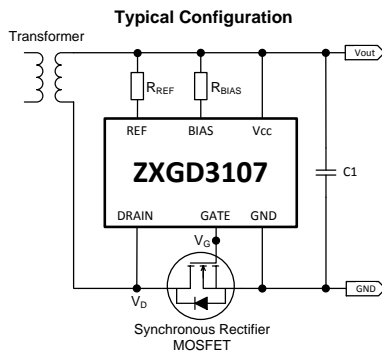
- Telecoms PSU
- Laptop Adaptors
- Computing Power Supplies – ATX and Server PSU

**Features**

- Proportional Gate Drive to Minimize Body Diode Conduction
- Low Standby Power with Quiescent Supply Current < 1mA
- 4.5V Operation Enables Low Voltage Supply
- 40V  $V_{CC}$  Rating
- 200V Drain Voltage Rating
- Operation up to 500kHz
- Critical Conduction Mode (CrCM) & Continuous Mode (CCM)
- Compliant with Eco-Design Directive
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony free. "Green" Device (Note 3)**

**Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Solderable per MIL-STD-202, Method 208 Ⓔ3
- Weight: 0.074 grams (Approximate)

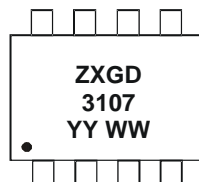


Pin Name	Pin Function
V <sub>CC</sub>	Power Supply
DNC	Do Not Connect
BIAS	Bias Current
DRAIN	Drain Sense
REF	Reference Current
GND	Power Ground
GATE	Gate Drive

**Ordering Information (Note 4)**

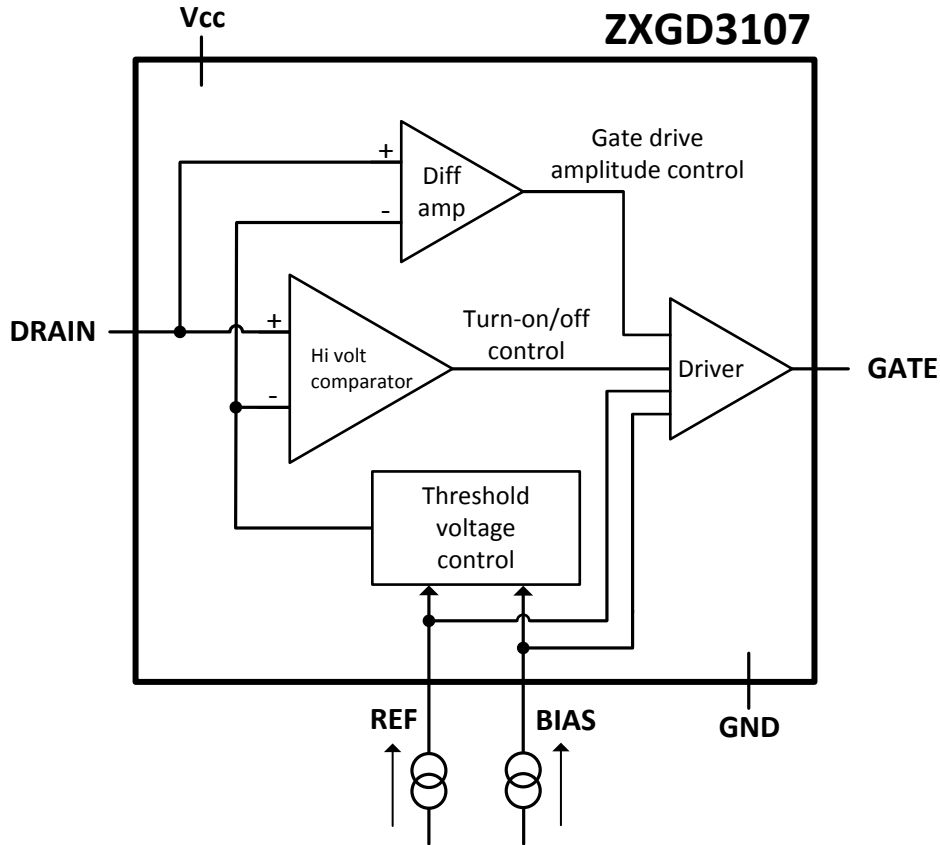
Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXGD3107N8TC	ZXGD3107	13	12	2,500

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com>.

**Marking Information**


- ZXGD = Product Type Marking Code, Line 1
- 3107 = Product Type Marking Code, Line 2
- YY = Year (ex: 15 = 2015)
- WW = Week (01 - 53)

**Functional Block Diagram**



Pin #	Pin Name	Pin Function and Description
1	Vcc	<b>Power supply</b> This supply pin should be closely decoupled to ground with a ceramic capacitor.
2	DNC	<b>Do Not Connect</b> Leave pin floating.
3	BIAS	<b>Bias</b> Connect this pin to Vcc via R <sub>BIAS</sub> resistor. Select R <sub>BIAS</sub> to source 0.56mA into this pin. Refer to Table 1 and 2, in Application Information section.
4	DRAIN	<b>Drain sense</b> Connect directly to the synchronous MOSFET drain terminal.
5	REF	<b>Reference</b> Connect this pin to Vcc via R <sub>REF</sub> resistor. Select R <sub>REF</sub> to source 1.23mA into this pin. Refer to Table 1 and 2, in Application Information section.
6	DNC	<b>Do not connect</b> Leave pin floating.
7	GND	<b>Ground</b> Connect this pin to the synchronous MOSFET source terminal and ground reference point.
8	GATE	<b>Gate drive</b> This pin sinks and sources the I <sub>SINK</sub> and I <sub>SOURCE</sub> current to the synchronous MOSFET Gate.

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Supply Voltage, relative to GND	V <sub>CC</sub>	40	V
Drain Pin Voltage	V <sub>D</sub>	-3 to 200	V
Gate Output Voltage	V <sub>G</sub>	-3 to V <sub>CC</sub> + 3	V
Gate Driver Peak Source Current	I <sub>SOURCE</sub>	4	A
Gate Driver Peak Sink Current	I <sub>SINK</sub>	9	A
Reference Voltage	V <sub>REF</sub>	V <sub>CC</sub>	V
Reference Current	I <sub>REF</sub>	25	mA
Bias Voltage	V <sub>BIAS</sub>	V <sub>CC</sub>	V
Bias Current	I <sub>BIAS</sub>	100	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	P <sub>D</sub>	490	mW mW/°C
		3.92	
		655	
		5.24	
		720	
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	5.76	°C/W
		785	
		6.28	
		255	
Thermal Resistance, Junction to Lead	R <sub>θJL</sub>	191	°C/W
		173	
		159	
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	55	°C/W
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	45	°C/W
Operating Temperature Range	T <sub>J</sub>	-40 to +150	°C
Storage Temperature Range	T <sub>STG</sub>	-50 to +150	

**ESD Ratings** (Note 11)

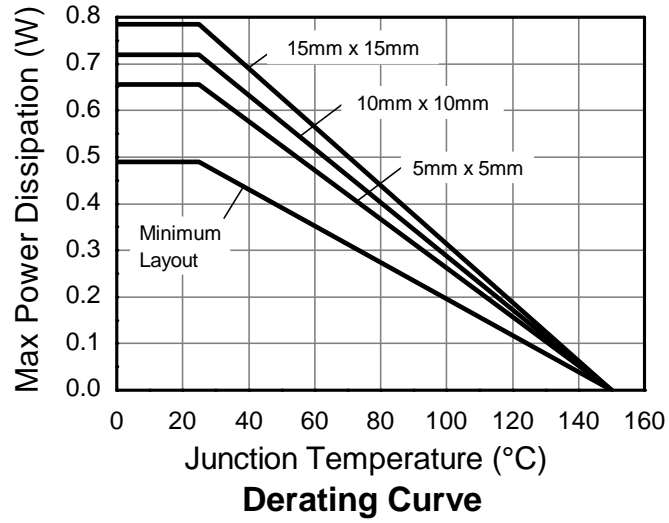
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	1,500	V	1C
Electrostatic Discharge - Machine Model	ESD MM	200	V	B

- Notes:
- For a device surface mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  - Same as note (5), except pin 1 (V<sub>CC</sub>) and pin 7 (GND) are both connected to separate 5mm x 5mm 1oz copper heatsinks.
  - Same as note (6), except both heatsinks are 10mm x 10mm.
  - Same as note (6), except both heatsinks are 15mm x 15mm.
  - Thermal resistance from junction to solder-point at the end of each lead on pin 1 (V<sub>CC</sub>) or pin 7 (GND).
  - Thermal resistance from junction to top of the case.
  - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

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**Thermal Derating Curve**

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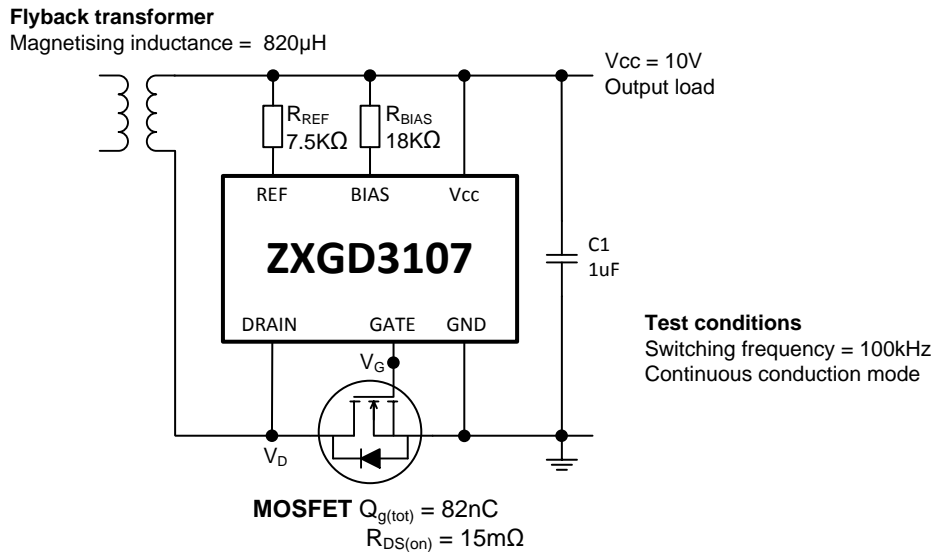


**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

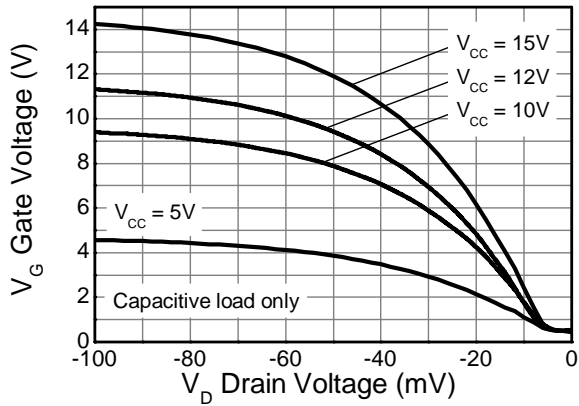
V<sub>CC</sub> = 10V; R<sub>BIAS</sub> = 18kΩ (I<sub>BIAS</sub> = 0.56mA); R<sub>REF</sub> = 7.5kΩ (I<sub>REF</sub> = 1.23mA)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>Input Supply</b>						
Supply to GND Voltage	V <sub>CC(ON)</sub>	40	-	-	V	V <sub>D</sub> = -100mV @ I <sub>CC</sub> = 10μA
Supply to GND Voltage	V <sub>CC(OFF)</sub>	40	-	-	V	V <sub>D</sub> = 1V @ I <sub>CC</sub> = 10μA
Drain to GND Voltage	V <sub>D</sub>	200	-	-	V	I <sub>D</sub> = 1μA
Quiescent Current	I <sub>Q</sub>	-	1.79	-	mA	V <sub>D</sub> ≥ 0mV
<b>Gate Driver</b>						
Gate Peak Source Current	I <sub>SOURCE</sub>	-	2	-	A	Capacitive load: C <sub>L</sub> = 20nF
Gate Peak Sink Current	I <sub>SINK</sub>	-	7	-		
<b>Detector under DC condition</b>						
Turn-off Threshold Voltage	V <sub>T</sub>	-20	-10	0	mV	V <sub>G</sub> = 1V
Gate Output Voltage	V <sub>G(off)</sub>	-	0.2	0.6	V	V <sub>D</sub> ≥ 1V
	V <sub>G</sub>	5.0	7.8	-		V <sub>D</sub> = -50mV
		8.0	9.4	-		V <sub>D</sub> = -100mV
<b>Switching Performance</b>						
Turn-on Propagation Delay	t <sub>d(rise)</sub>	-	70	-	ns	Rise and fall measured 10% to 90% Refer to application test circuit below
Gate Rise Time	t <sub>r</sub>	-	175	-		
Turn-off Propagation Delay	t <sub>d(fall)</sub>	-	15	-		
Gate Fall Time	t <sub>f</sub>	-	20	-		

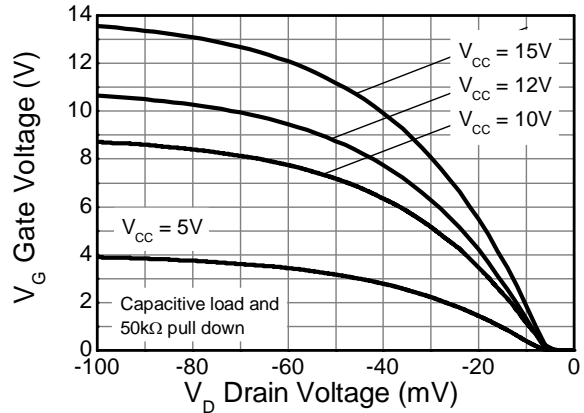
**Test Circuit for Switching Performance**



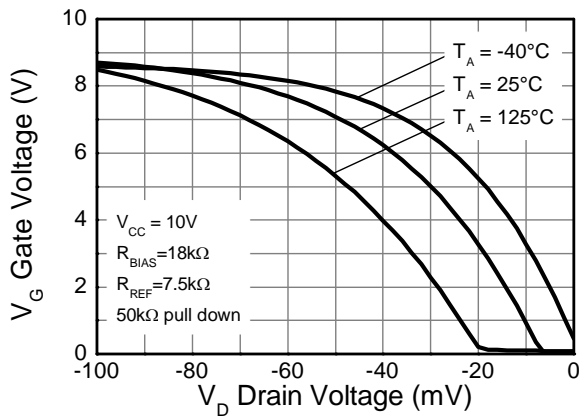
**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



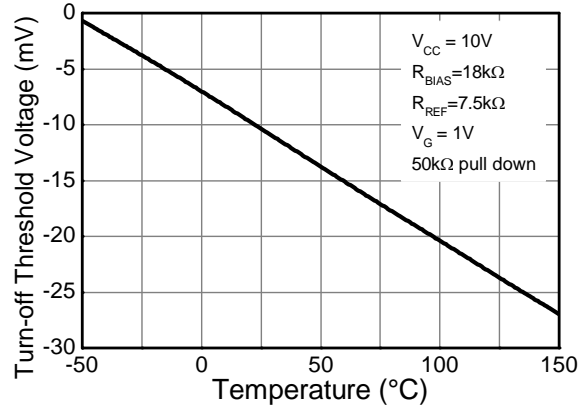
**Transfer Characteristic**



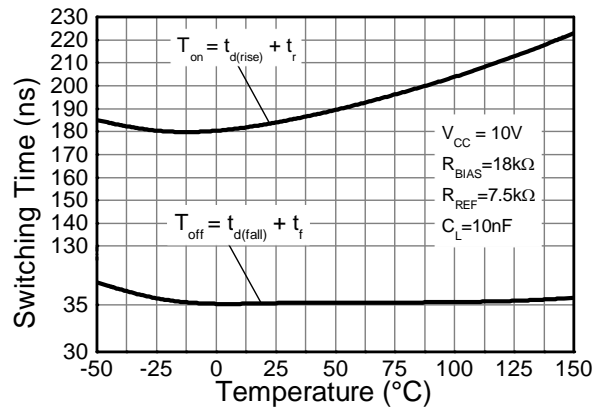
**Transfer Characteristic**



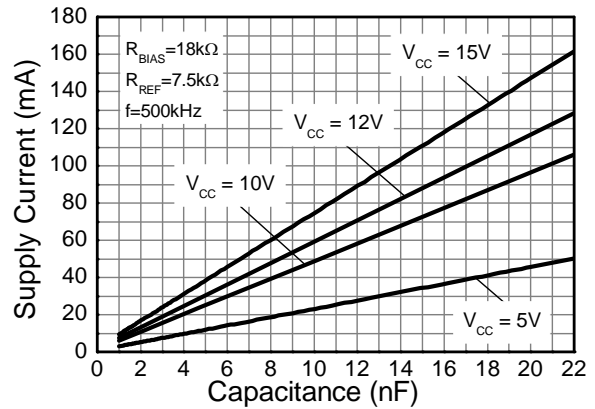
**Transfer Characteristic**



**Turn-off Threshold Voltage vs Temperature**

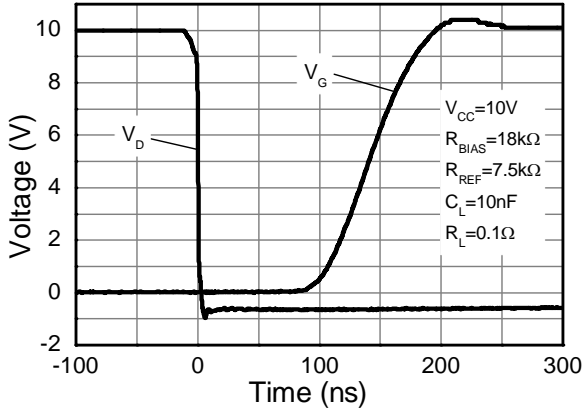


**Switching vs Temperature**

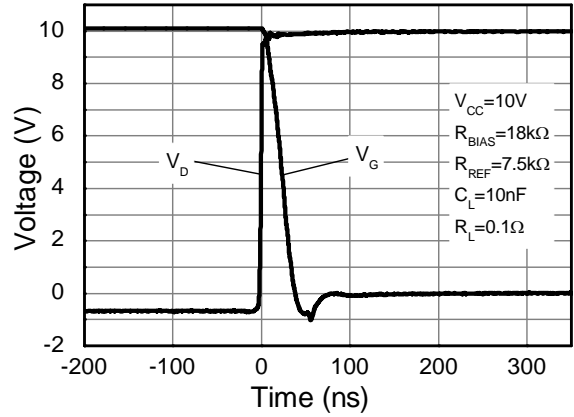


**Supply Current vs Capacitive Load**

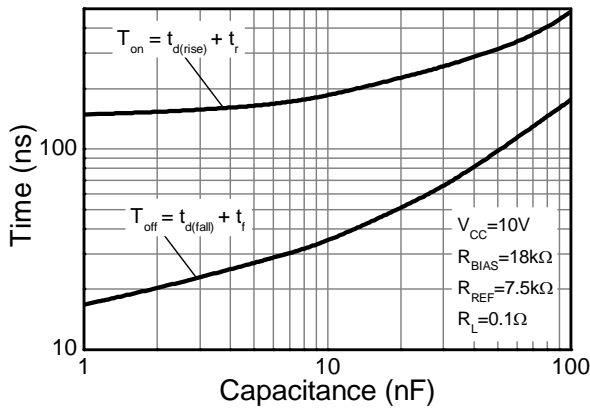
**Typical Electrical Characteristics** (continued) (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



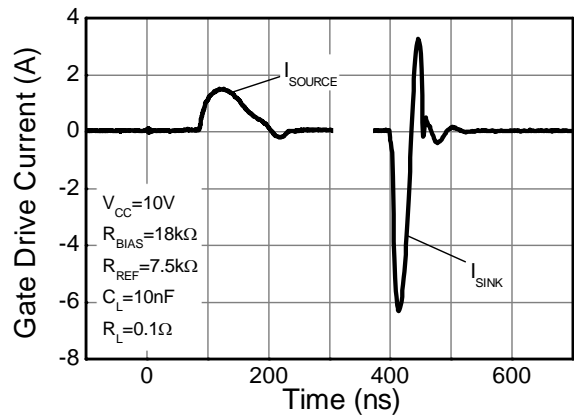
**Switch On Speed**



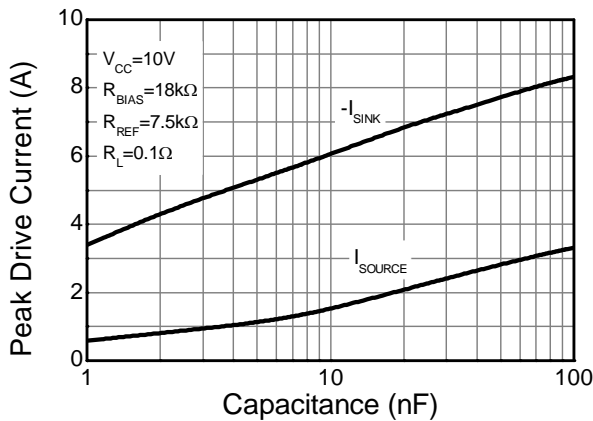
**Switch Off Speed**



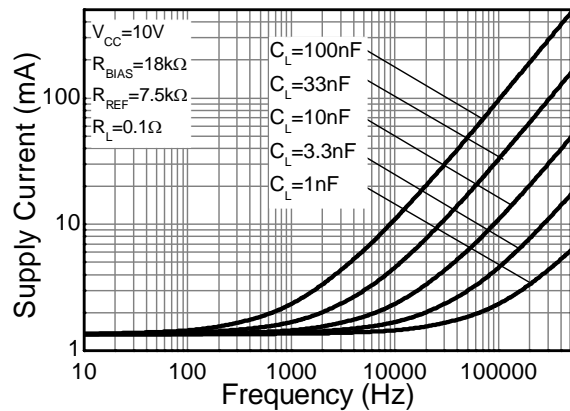
**Switching vs Capacitive Load**



**Gate Drive Current**



**Gate Current vs Capacitive Load**



**Supply Current vs Frequency**

## Application Information

The purpose of the ZXGD3107 is to drive a MOSFET as a low- $V_F$  Schottky diode replacement in isolated AC-DC converter. When combined with a low  $R_{DS(ON)}$  MOSFET, the controller can yield significant power-efficiency improvement, while maintaining design simplicity and incurring minimal component count. Figure 1 shows the typical configuration of ZXGD3107 for synchronous rectification in a low output voltage flyback converter.

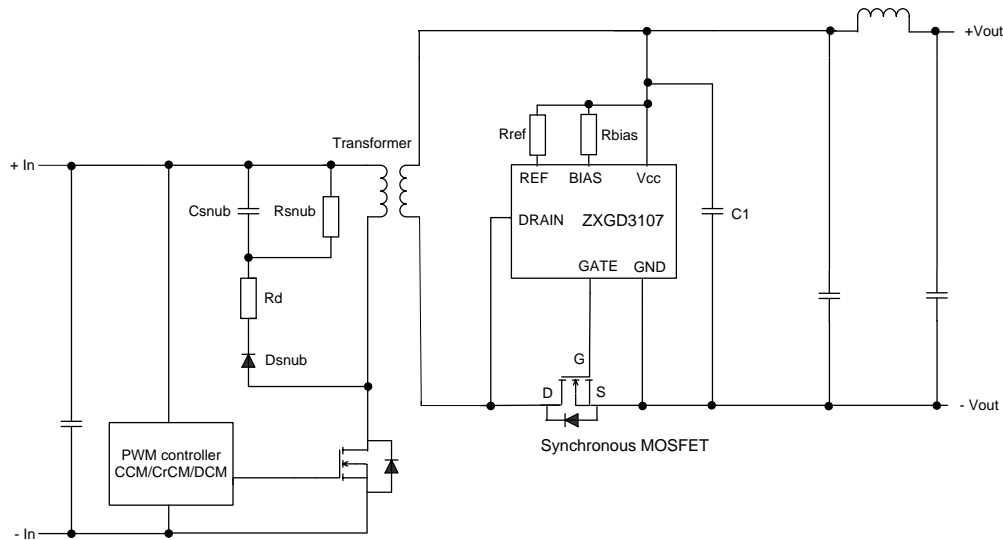


Figure 1 - Typical flyback application schematic

## Threshold Voltage and Resistor Setting

Proper selection of external resistors  $R_{REF}$  and  $R_{BIAS}$  is important for optimum device operation.  $R_{REF}$  and  $R_{BIAS}$  supply fixed current into the  $I_{REF}$  and  $I_{BIAS}$  pin of the controller.  $I_{REF}$  and  $I_{BIAS}$  combines to set the turn-off threshold voltage level,  $V_T$ . In order to set  $V_T$  to  $-10mV$ , the recommended  $I_{REF}$  and  $I_{BIAS}$  are  $1.23mA$  and  $0.56mA$  respectively.

The values for  $R_{REF}$  and  $R_{BIAS}$  are selected based on the  $V_{CC}$  voltage. If the  $V_{CC}$  pin is connected to the power converter's output, the resistors should be selected based on the nominal converter's output voltage. Table 1 provides the recommended resistor values for different  $V_{CC}$  voltages to achieve a  $V_T$  of  $-10mV$ .

Supply, $V_{CC}$	Bias Resistor, $R_{BIAS}$	Reference Resistor, $R_{REF}$
5V	9.6k $\Omega$	4k $\Omega$
10V	18k $\Omega$	7.5k $\Omega$
12V	24k $\Omega$	9.6k $\Omega$
15V	30k $\Omega$	12k $\Omega$

Table 1 – Recommended resistor values for different  $V_{CC}$  voltages



**Application Information** (continued)

**Functional Descriptions**

The operation of the device is described step-by-step with reference to the timing diagram in Figure 2.

1. The detector stage monitors the MOSFET drain-source voltage.
2. When, due to transformer action, the MOSFET body diode is forced to conduct there is a negative voltage on the drain pin due to the body diode forward voltage.
3. When the negative drain voltage crosses the turn-off Threshold voltage  $V_T$ , the detector stage outputs a positive voltage with respect to ground after the turn-on delay time  $t_{d(\text{fall})}$ . This voltage is then fed to the MOSFET driver stage and current is sourced out of the GATE pin.
4. The controller goes into Proportional Gate drive control — the Gate output voltage is proportional to the MOSFET on-resistance-induced drain-source voltage. Proportional Gate drive ensures that MOSFET conducts during majority of the conduction cycle to minimize power loss in the body diode.
5. As the drain current decays linearly toward zero, Proportional Gate drive control reduces the Gate voltage so the MOSFET can be turned off rapidly at zero current crossing. The Gate voltage falls to 1V when the drain-source voltage crosses the detection threshold voltage to minimize reverse current flow.
6. At zero drain current, the controller Gate output voltage is pulled low to  $V_{G(\text{off})}$  to ensure that the MOSFET is off.

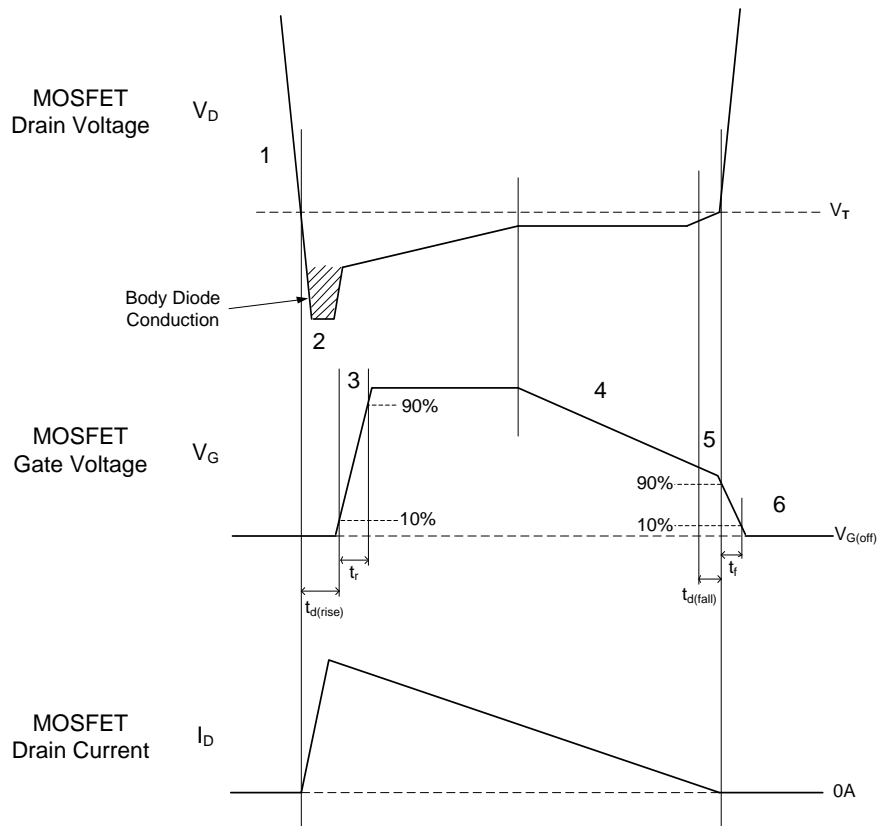


Figure 2 - Timing diagram for a critical conduction mode flyback converter

**Application Information** (cont.)

**Gate Driver**

The controller is provided with single channel high-current Gate drive output, capable of driving one or more N-channel power MOSFETs. The controller can operate from Vcc of 4.5V to drive both standard MOSFETs and logic level MOSFETs.

The GATE pin should be as close to the MOSFET's Gate as possible. A resistor in series with GATE pin helps to control the rise time and decrease switching losses due to Gate voltage oscillation. A diode in parallel to the resistor is typically used to maintain fast discharge of the MOSFET's Gate.

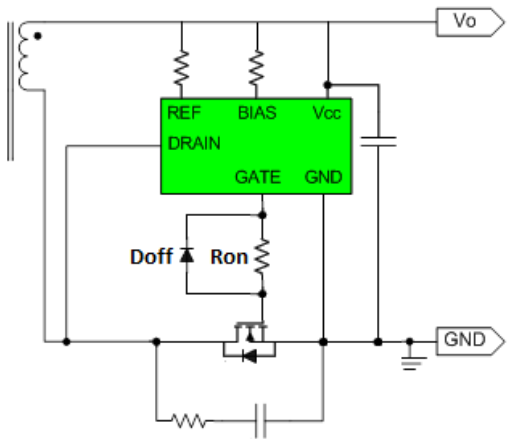


Figure 3 - Typical connection of the ZXGD3107 to the synchronous MOSFET

**Quiescent Current Consumption**

The quiescent current consumption of the controller is the sum of I<sub>REF</sub> and I<sub>BIAS</sub>. For an application that requires ultra-low standby power consumption, I<sub>REF</sub> and I<sub>BIAS</sub> can be further reduced by increasing the value of resistor R<sub>REF</sub> and R<sub>BIAS</sub>.

Bias Current I <sub>BIAS</sub>	Ref Current I <sub>REF</sub>	Bias Resistor R <sub>BIAS</sub>	Ref Resistor R <sub>REF</sub>	Quiescent Current I <sub>q</sub>
0.25	0.78	39.8kΩ	11.9kΩ	1.03mA
0.35	0.94	28.4kΩ	9.8kΩ	1.29mA
0.45	1.1	22.1kΩ	8.4kΩ	1.55mA
0.56	1.23	18kΩ	7.5kΩ	1.79mA
0.6	1.34	16.6kΩ	6.9kΩ	1.94mA
0.8	1.6	12.4kΩ	5.8kΩ	2.4mA

Table 2 – Quiescent current consumption for different resistor values at Vcc=10V

I<sub>REF</sub> also controls the Gate driver peak sink current whilst I<sub>BIAS</sub> controls the peak source current. At the default current value of I<sub>REF</sub> and I<sub>BIAS</sub> of 1.23mA and 0.56mA, the Gate driver is able to provide 2A source and 6A sink current. The Gate current decreases if I<sub>REF</sub> and I<sub>BIAS</sub> are reduced. Care must be taken in reducing the controller quiescent current so that sufficient drive current is still delivered to the MOSFET particularly for high-switching frequency application.

**Application Information** (cont.)

**Layout Guidelines**

When laying out the PCB, care must be taken in decoupling the ZXGD3107 closely to V<sub>CC</sub> and ground with 1μF low-ESR, low-ESL X7R type ceramic bypass capacitor. If the converter's output voltage is higher than 40V, a series voltage regulator between the converter's output voltage and the V<sub>CC</sub> pin can be used to get a stable V<sub>CC</sub> voltage.

GND is the ground reference for the internal high-voltage amplifier as well as the current return for the Gate driver. So the ground return loop should be as short as possible. Sufficient PCB copper area should be allocated to the V<sub>CC</sub> and GND pin for heat dissipation especially for high-switching frequency application.

Any stray inductance involved by the load current may cause distortion of the drain-to-source voltage waveform, leading to premature turn-off of the synchronous MOSFET. In order to avoid this issue, drain-voltage sensing should be done as physically close to the drain terminals as possible. The PCB track length between the controller drain pin and MOSFET's terminal should be kept less than 10mm. MOSFET packages with low internal-wire-bond inductance are preferred for high-switching frequency power conversion to minimize body diode conduction.

After the primary MOSFET turns-off, its drain voltage oscillates due to reverse recovery of the snubber diode. These high-frequency oscillations are reflected across the transformer to the drain terminal of the synchronous MOSFET. The synchronous controller senses the drain-voltage ringing, causing its Gate output voltage to oscillate. The synchronous MOSFET cannot be fully enhanced until the drain voltage stabilizes.

In order to prevent this issue, the oscillations on the primary MOSFET can be damped with either a series resistor R<sub>d</sub> to the snubber diode or an R-C network across the diode. Both methods reduce the oscillations by softening the snubber diode's reverse recovery characteristic.

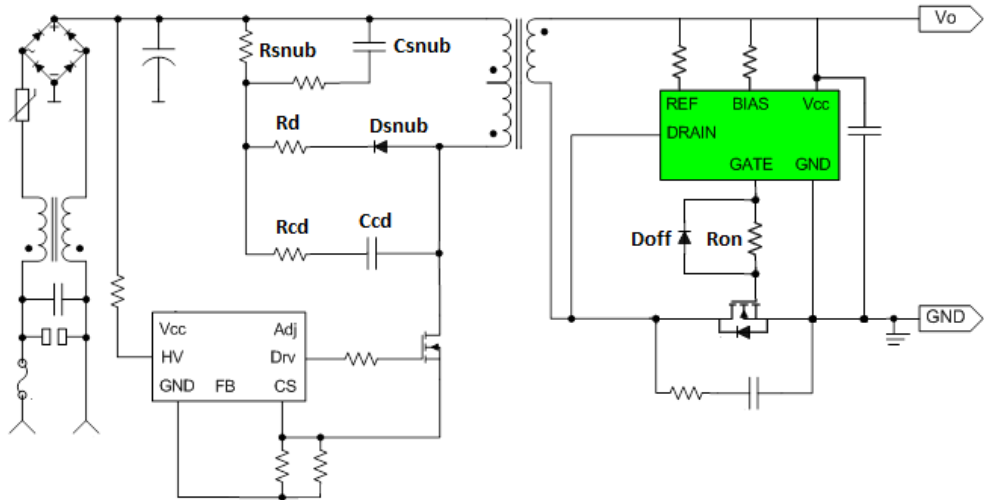
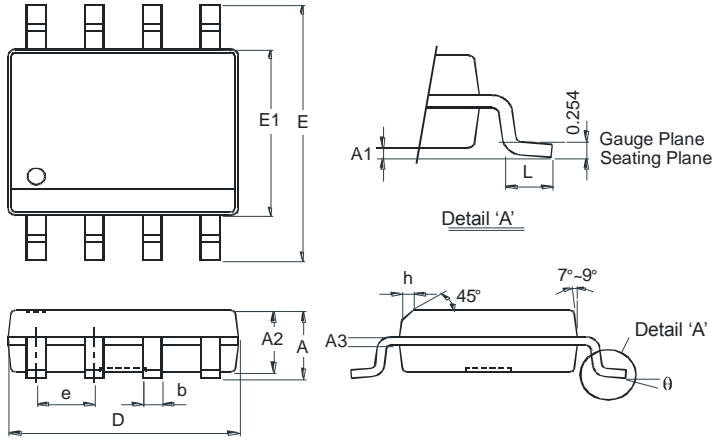


Figure 4 - Primary side snubber network to reduce drain voltage oscillations

**Package Outline Dimensions**

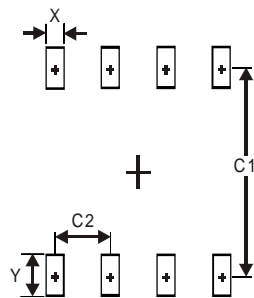
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



## JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели,  
кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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